TECHNICAL DATA
DATA SHEET 698, REV. -

DUAL HERMETIC POWER MOSFET N-CHANNEL

- **200 VOLT, 0.4 OHM, 9.0A MOSFET**
- **Fast Switching**
- **Low $R_{DS\ (on)}$**
- **Equivalent to IRF230**

MAXIMUM RATINGS

ALL RATINGS ARE AT T_A = 25°C UNLESS OTHERWISE SPECIFIED.

RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE	V_{GS}	-	-	±20	Volts
CONTINUOUS DRAIN CURRENT @ T_C = 25°C	I_D	-	-	9.0	Amps
PULSED DRAIN CURRENT @ T_C = 25°C	I_{DM}	-	-	36	Amps(pk)
OPERATING AND STORAGE TEMPERATURE	T_{OP}/T_{STG}	-55	-	+150	°C
TERMAL RESISTANCE JUNCTION TO CASE	$R_{\theta JC}$	-	-		°C/W
TOTAL DEVICE DISSIPATION @ T_C = 25°C	P_D	-	-		Watts

ELECTRICAL CHARACTERISTICS

DRAIN TO SOURCE BREAKDOWN VOLTAGE V_{GS} = 0V, I_D = 1.0mA	BV_{DSS}	200	-	-	Volts
GATE THRESHOLD VOLTAGE $V_{DS} = V_{GS}$, I_D = 250µA	$V_{GS(th)}$	2.0	-	4.0	Volts
DRAIN TO SOURCE ON STATE RESISTANCE V_{GS} = 10Vdc, I_D = 6.0A I_D = 9.0A	$R_{DS(ON)}$	-	-	0.4 0.49	Ω
ZERO GATE VOLTAGE DRAIN CURRENT V_{DS} = 0.8xMax. Rating, V_{GS} = 0Vdc V_{DS} = 0.8xMax. Rating V_{GS} = 0Vdc, T_J = 125°C	I_{DSS}	-	-	25 250	µA
GATE TO BODY LEAKAGE CURRENT V_{GS} = ±20Vdc,	I_{GSS}	-	-	±100	nA
TOTAL GATE CHARGE V_{GS} = 10 Vdc GATE TO SOURCE CHARGE V_{DS} = 0.5V Max. Rating, GATE TO DRAIN CHARGE I_D = 9.0A	Q_g Q_{gs} Q_{gd}	16 3.0 8.0	-	39 5.7 20	nC
TURN ON DELAY TIME V_{DD} = 100V, RISE TIME I_D = 9.0A, TURN OFF DELAY TIME R_G = 7.5Ω FALL TIME V_{GS} = 10V	$t_{d(ON)}$ t_r $t_{d(OFF)}$ t_f	-	-	35 80 60 40	nsec
FORWARD VOLTAGE T_J = 125°C, I_S = 9.0A, V_{GS} = 0V	V_{SD}	-	-	1.4	Volts
REVERSE RECOVERY TIME I_F = 9.0A, REVERSE RECOVERY CHARGE di/dt ≤ 100A/µsec, V_{DD} ≤ 50V	t_{rr}	-	-	500	nsec
INPUT CAPACITANCE V_{DS} = 25 Vdc, OUTPUT CAPACITANCE V_{GS} = 0 Vdc, REVERSE TRANSFER CAPACITANCE f = 1 MHz	C_{iss} C_{oss} C_{rss}	-	600 250 80	-	pF

SENSITRON

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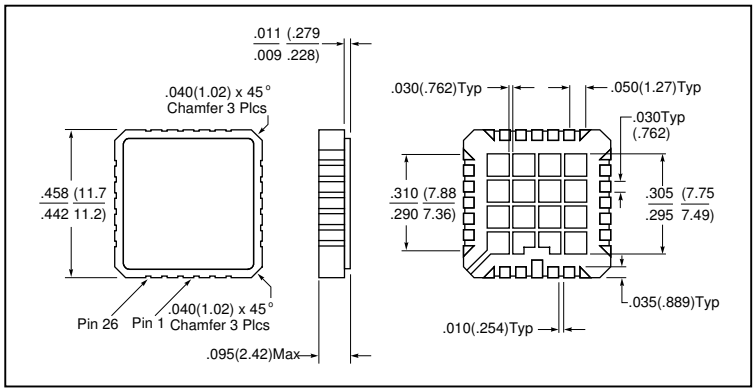
MECHANICAL DIMENSIONS: in Inches / mm



LCC-28T

PINOUTS

DEVICE TYPE	PIN(S) 1 & 15~28	PINS 5~11	PINS 2, 3, 13, 14
DUAL MOSFET - LCC-28T	SOURCE	DRAIN	GATE

TECHNICAL DATA

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